

In the Claims:

Kindly add the following new claims 28-33, as follows:

28. (New) The device according to claim 23, wherein said extension regions extend further under the spacers than said diffusion regions.
29. (New) The device according to claim 23, wherein said metal layer and said exposed portion of the extension region form a Schottky diode.
30. (New) The device according to claim 29, wherein said metal layer extends into the semiconductor layer.
31. (New) The device according to claim 30, wherein said metal layer extends into a portion of the semiconductor layer below said extension regions.
32. (New) An integrated circuit disposed on an SOI substrate having a body region, comprising a transistor having a source diffusion region, a gate formed over said body region, a first sidewall spacer disposed on a sidewall of said gate abutting said source diffusion region, a drain diffusion region, a second sidewall spacer disposed on a sidewall of said gate abutting said drain diffusion region, wherein said first sidewall spacer is thinner than said second sidewall spacer, and extension diffusion regions that extend further under said gate than said source diffusion region or said drain diffusion region, said extension diffusion regions having a dopant concentration less than that of said source diffusion region and said drain diffusion region; and a conductor in contact with at least a portion of at least one of said extension regions and at least a portion of said source diffusion region to form a Schottky diode that prevents charge from accumulating in said body region.
33. (New) The device of claim 32 wherein said conductor is in contact with said body region.

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